

AMENDMENT TO THE CLAIMS:

1 - 39 (Cancelled)

40. (Original) A poly-poly capacitor comprising a bottom polysilicon electrode formed over isolation regions that are present in a Si-containing substrate; a high-k dielectric having a dielectric constant of greater than about 8 formed on a portion of said bottom electrode; and a doped Si-containing electrode formed on said high-k dielectric, wherein said doped Si-containing electrode comprises an intrinsic base polysilicon layer of a bipolar device.

41. (Original) The poly-poly capacitor of Claim 40 wherein said bottom polysilicon electrode is composed of poly SiGe.

42. (Original) The poly-poly capacitor of Claim 40 wherein said high-k dielectric is a binary metal oxide, a silicate, aluminate or oxynitride of a binary metal oxide, or a perovskite oxide.

43. (Original) The poly-poly capacitor of Claim 42 wherein said high-k dielectric is a binary metal oxide or an aluminate of a binary metal oxide.

44. (Original) The poly-poly capacitor of Claim 43 wherein said high-k dielectric is Al_2O_3 .

45. (Original) The poly-poly capacitor of Claim 40 wherein said doped Si-containing electrode is comprised of poly SiGe.